

### 1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



**Product data sheet** 

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

### 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- High commutation capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

### 3. Applications

- AC solenoids
- General purpose motor control circuits
- Home appliances

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	25	А
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 107$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	4	А
Static characte	eristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-;	-	-	10	mA
		T <sub>j</sub> = 25 °C; <u>Fig. 7</u>				

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2	1 7 9	sym051
3	G	gate		·
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BTA204-600E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

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## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 107 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	4	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	25	Α
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 16.7  \text{ms}$	-	27	Α
l <sup>2</sup> t	I2t for fusing	t <sub>p</sub> = 10 ms; SIN	-	3.1	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 6 \text{ A}$ ; $I_G = 0.2 \text{ A}$ ; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

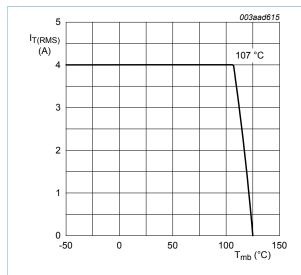
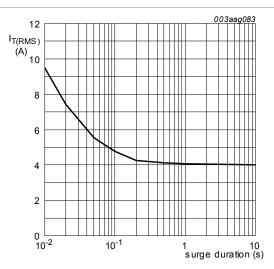


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 107 \text{ }^{\circ}\text{C}$ 

Fig. 2. RMS on-state current as a function of surge duration; maximum values

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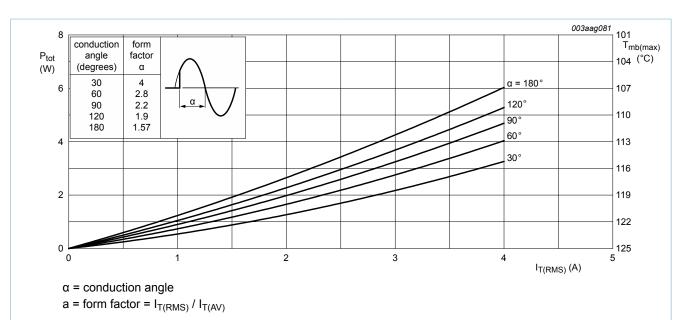


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

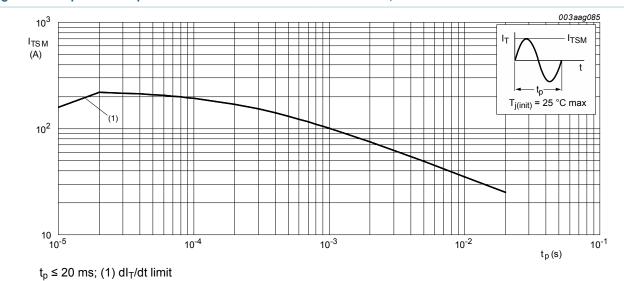


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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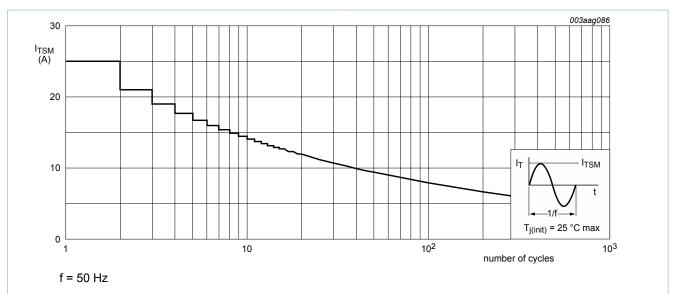


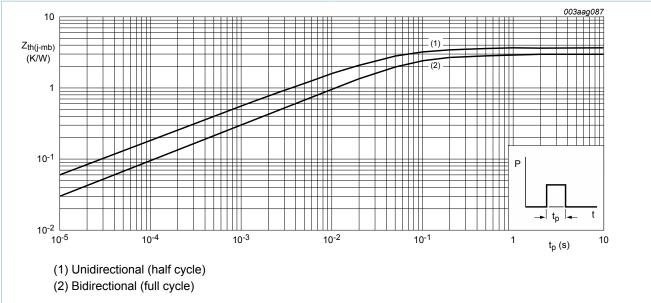
Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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### 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	full cycle; Fig. 6	-	-	3	K/W
	from junction to mounting base	half cycle; Fig. 6	-	-	3.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



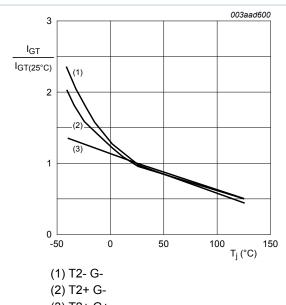
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## 9. Characteristics

#### Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			
I <sub>GT</sub> gate trigger current	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	10	mA
	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	10	mA	
I <sub>L</sub> latching current	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	12	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	18	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	12	mA
l <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	12	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
V <sub>GT</sub> ga	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic cl	naracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	30	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 4 A; $dV_{com}/dt$ = 0.1 V/µs; gate open circuit	8	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 4 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; \text{ gate open circuit}$	2.1	-	-	A/ms

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(3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

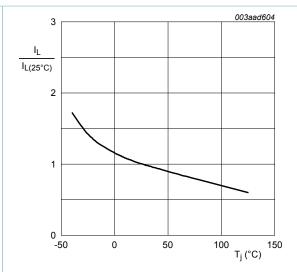


Fig. 8. Normalized latching current as a function of junction temperature

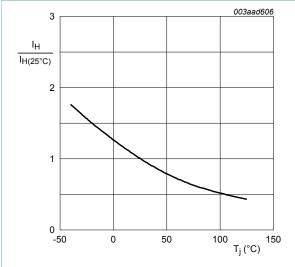
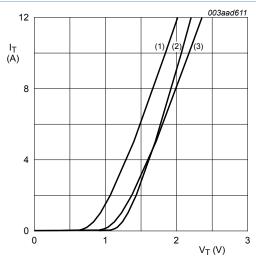


Fig. 9. Normalized holding current as a function of junction temperature

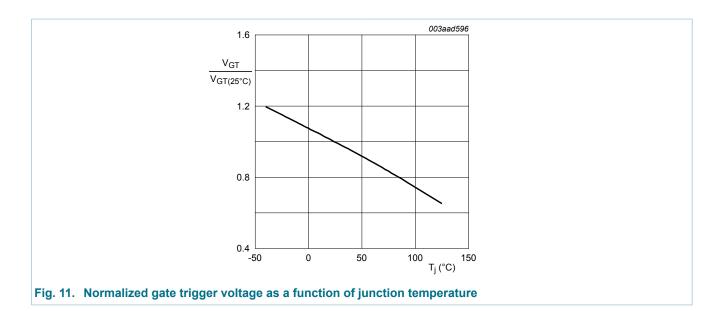


 $V_{o}$  = 1.27 V;  $R_{s}$  = 0.091  $\Omega$ 

Fig. 10. On-state current as a function of on-state voltage

<sup>(3)</sup> T<sub>i</sub> = 25 °C; maximum values

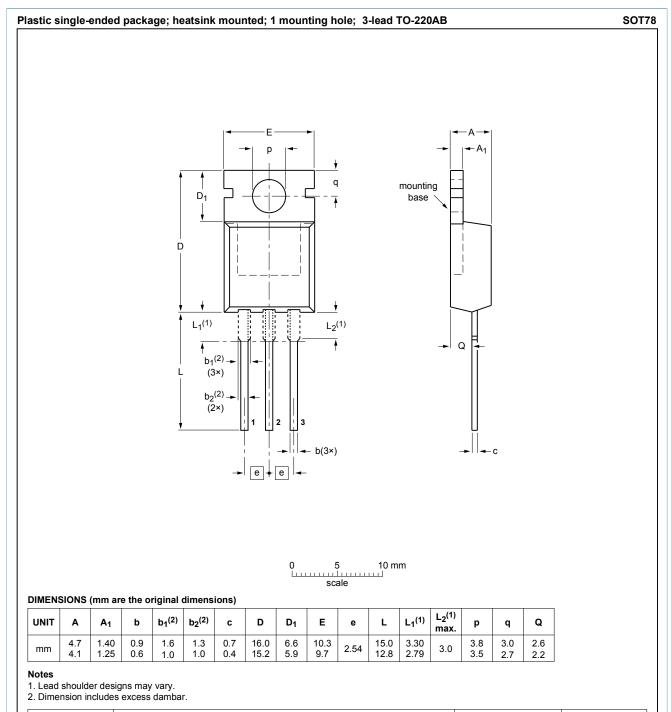
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9/13

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## 10. Package outline



OUTLINE		REFER	ENCES	EUROPEAN ISSUE DA	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

Fig. 12. Package outline TO-220AB (SOT78)

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# BTA204-600E

**3Q Hi-Com Triac** 

### 12. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	
5	Pinning information	2
6	Ordering information	
7	Limiting values	
8	Thermal characteristics	
9	Characteristics	7
10	Package outline	10
11	Legal information	
11.1	Data sheet status	11
11.2	Definitions	11
11.3	Disclaimers	11
11.4	Trademarks	12

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